Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Canceled).

2. (Currently Amended) The component as claimed in claim 26, wherein ~~that~~ a side of the radiation-generating layer (2) which is remote from the substrate (1) is provided for [[the]] mounting of the component.

3. (Currently Amended) The component as claimed in claim 2, wherein a mounting area is formed on ~~that~~ the side of the radiation-generating layer [[(2)]] which is remote from the substrate [[(1)]].

4. (Currently Amended) The component as claimed in claim 26, wherein the perpendicular side areas [[(5)]] form a base [[(6)]] on the underside of the substrate, the inclined side areas [[(3)]] adjoining [[the]] a top side of said base.

5. (Currently Amended) The component as claimed in claim 4, wherein [[the]] an upper boundary of the unilluminated region [[(4)]] coincides with [[the]] an upper boundary of the base [[(6)]].

6. (Currently Amended) The component as claimed in claim 4, wherein the height (h) of the base [[(6)]] is between 15 and 30 μm.

7. (Currently Amended) The component as claimed in claim 26, wherein the inclined side areas [[(3)]] form an angle (α) of between 15 and 40° with the underside of the substrate.

8. (Currently Amended) The component as claimed in claim 26, wherein the substrate [[(1)]] has a width (B) of between 300 and 2000 μm on the underside.

9. (Currently Amended) The component as claimed in claim 26, wherein the substrate [[(1)]] has a thickness (D) of between 200 and 300 μm.

10. (Currently Amended) The component as claimed in claim 26, wherein the radiation-generating layer [[(2)]] covers the underside of the substrate apart from an outer free edge [[(7)]] having a width (bF) of between 10 and 50 μm.

11. (Currently Amended) The component as claimed in claim 26, wherein the radiation-generating layer [[(2)]] has bevelled side edges [[(8)]], which reflect [[the]] light emitted laterally with respect to the substrate [[(1)]] in the direction of the substrate [[(1)]].

12. (Currently Amended) The component as claimed in claim 11, wherein the bevelled side edges [[(8)]] form an angle (β) of between 20 and 70° with the underside of the substrate.

13. (Currently Amended) The component as claimed in claim 11, wherein the bevelled edges [[(8)]] of the radiation-generating layer [[(2)]] form with the substrate [[(1)]] an angle (β) suitable for a total reflection of the ~~radiation~~ light at the side edges [[(12)]].

14. (Currently Amended) The component as claimed in claim 11, wherein the side edges [[(12)]] of the radiation-generating layer [[(2)]] are covered with an optically reflective material [[(9)]].

15. (Currently Amended) The component as claimed in claim 14, wherein the optically reflective material [[(9)]] is aluminum or silver.

16. (Currently Amended) The component as claimed in claim 26, wherein

contact elements ~~(10, 10a)~~ are arranged on the top side of the substrate [[(1)]],

[[the]] a transverse conductivity of the substrate [[(1)]] leads to a conical extension of a current coupled into the substrate [[(1)]] from the contact ~~element (10)~~ elements, and

the contact elements [[(10)]] are spaced apart from one another in such a way that [[the]] current expansion cones [[(13)]] touch one another at a depth (T) at which the entire cross-sectional area of the substrate [[(1)]] is energized.

17. (Currently Amended) The component as claimed in claim 16, wherein the contact elements are interconnects [[(10)]] running along nested squares [[(11)]], the squares [[(11)]] having equidistant side edges [[(12)]] parallel to one another.

18. (Currently Amended) The component as claimed in claim 17, wherein the interconnects [[(10)]] have widths (bL1, bL2, bL3) that differ from one another in accordance with [[the]] a surface of the substrate [[(1)]] that is to be energized.

19. (Currently Amended) The component as claimed in claim 26, wherein the substrate [[(1)]] contains silicon carbide.

20. (Currently Amended) The component as claimed in claim 26, wherein the substrate [[(1)]] contains hexagonal 6H silicon carbide.

21. (Currently Amended) The component as claimed in claim 26, wherein the radiation-generating layer [[(2)]] contains gallium nitride.

22. (Currently Amended) The component as claimed in claim 26, wherein the underside of the substrate has a width (B) of at least 300 μm.

23. (Currently Amended) A method for producing a radiation-emitting semiconductor component as claimed in claim 26, the method having the following steps:

a) sawing [[of]] V-shaped trenches [[(14)]] into a radiation-transmissive substrate [[(1)]] by means of a suitably shaped saw, a residual thickness (dr) of the substrate [[(1)]] remaining throughout,

b) ~~singulation of~~ separating the substrate [[(1)]] into a multiplicity of individual substrates [[(15)]] along the trenches [[(14)]].

24. (Currently Amended) The method as claimed in claim 23, wherein the ~~singulation~~ separation is effected by means of a saw having a straight saw blade.

25. (Currently Amended) The method as claimed in claim 24, wherein the ~~singulation~~ separation is effected by breaking.

26. (Currently Amended) A radiation emitting semiconductor component comprising:

a radiation-transmissive substrate [[(1)]] with inclined side areas [[(3)]] and having a refractive index (n1),

a radiation generating layer [[(2)]] arranged on an underside of said substrate and having a refractive index (n2),

wherein the refractive index (n1) of the substrate [[(n1)]] is greater than the refractive index (n2) of the radiation generating layer [[(2)]], and the difference ~~therebetween~~ between the refractive indices of the substrate and the radiation generating layer results in an unilluminated substrate region [[(4)]] into which no photons are coupled directly from the radiation generating layer; ~~(2), and~~

wherein the substrate [[(1)]] has essentially perpendicular side areas [[(5)]] in the unilluminated region; and [[(4)]]

wherein the inclined side areas adjoin a top side of the substrate which is remote from the radiation generating layer and parallel to the underside of the substrate.

27. (New) A radiation emitting semiconductor component comprising:

a radiation-transmissive substrate with inclined side areas and having a refractive index (n1), and

a radiation generating layer arranged on an underside of said substrate and having a refractive index (n2),

wherein the refractive index (n1) of the substrate is greater than the refractive index (n2) of the radiation generating layer, and the difference between the indices of the substrate and the radiation generating layer results in an unilluminated substrate region into which no photons are coupled directly from the radiation generating layer,

wherein the substrate has essentially perpendicular side areas in the unilluminated region, and

wherein the radiation-generating layer has bevelled side edges, which reflect light emitted laterally with respect to the substrate in the direction of the substrate.

28. (New) A radiation emitting semiconductor component comprising:

a radiation-transmissive substrate with inclined side areas and having a refractive index (n1), and

a radiation generating layer arranged on an underside of said substrate and having a refractive index (n2),

wherein the refractive index (n1) of the substrate is greater than the refractive index (n2) of the radiation generating layer, and the difference between the indices of the substrate and the radiation generating layer results in an unilluminated substrate region into which no photons are coupled directly from the radiation generating layer,

wherein the substrate has essentially perpendicular side areas in the unilluminated region,

wherein contact elements are arranged on the top side of the substrate,

wherein the transverse conductivity of the substrate leads to a conical extension of a current coupled into the substrate from the contact element,

wherein the contact elements are spaced apart from one another in such a way that current expansion cones touch one another at a depth (T) at which the entire cross-sectional area of the substrate is energized,

wherein the contact elements are interconnects running along nested squares, the squares having equidistant side edges parallel to one another, and

wherein the interconnects have widths (bL1, bL2, bL3) that differ from one another in accordance with the surface of the substrate that is to be energized.